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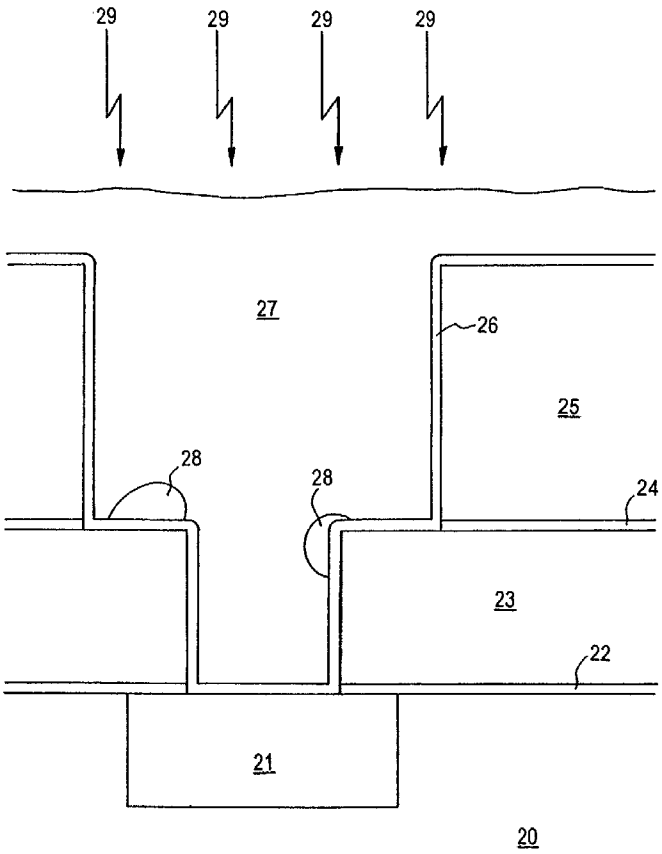
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(54) Title: METHOD OF FORMING RELIABLE CU INTERCONNECTS



(57) Abstract: Reliable Cu interconnects are formed by filling an opening in a dielectric layer (23, 25) with Cu (27) and then laser thermal annealing (29), in NH_3 to reduce copper oxide and to reflow the deposited Cu, thereby eliminating voids (28) and reducing contact resistance. Embodiments include laser thermal annealing (29) employing an NH_3 flow rate of about 200 to about 2,000 sccn.

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